



### FEATURES

- Double Side Cooling
- High Surge Capability

### APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

### VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages $V_{DRM}$ and $V_{RRM}$ V	Conditions
DCR1260F42 DCR1260F40	4200 4000	$T_{vj} = -40^{\circ}\text{C}$ to $125^{\circ}\text{C}$ , $I_{DRM} = I_{RRM} = 100\text{mA}$ , $V_{DRM}, V_{RRM} t_p = 10\text{ms}$ , $V_{DSM} \& V_{RSM} =$ $V_{DRM} \& V_{RRM} + 100\text{V}$ respectively

Lower voltage grades available.

### KEY PARAMETERS

$V_{DRM}$	<b>4200V</b>
$I_{T(AV)}$	<b>1255A</b>
$I_{TSM}$	<b>16800A</b>
$dV/dt^*$	<b>1500V/<math>\mu\text{s}</math></b>
$dI/dt$	<b>1000A/<math>\mu\text{s}</math></b>

\* Higher  $dV/dt$  selections available

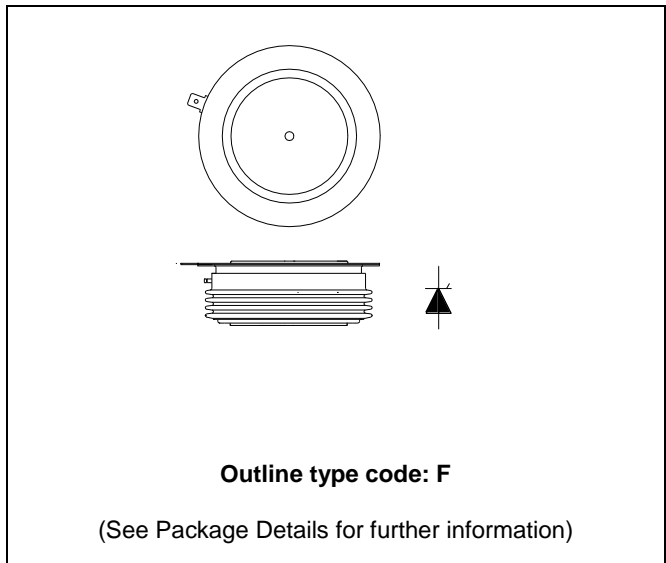


Fig. 1 Package outline

### ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

#### DCR1260F42

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

## CURRENT RATINGS

$T_{case} = 60^{\circ}\text{C}$  unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
<b>Double Side Cooled</b>				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	1260	A
$I_{T(RMS)}$	RMS value	-	1980	A
$I_T$	Continuous (direct) on-state current	-	1890	A

## SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
$I_{TSM}$	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}\text{C}$	16.8	kA
$I^2t$	$I^2t$ for fusing	$V_R = 0$	1.41	$\text{MA}^2\text{s}$

## THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions	Min.	Max.	Units	
$R_{th(j-c)}$	Thermal resistance – junction to case	Double side cooled	DC	-	0.0184	$^{\circ}\text{C/W}$
		Single side cooled	Anode DC	-	0.0333	$^{\circ}\text{C/W}$
			Cathode DC	-	0.0418	$^{\circ}\text{C/W}$
$R_{th(c-h)}$	Thermal resistance – case to heatsink	Clamping force 23kN (with mounting compound)	Double side	-	0.004	$^{\circ}\text{C/W}$
			Single side	-	0.008	$^{\circ}\text{C/W}$
$T_{vj}$	Virtual junction temperature	Blocking $V_{DRM} / V_{RRM}$	-	125	$^{\circ}\text{C}$	
$T_{stg}$	Storage temperature range		-55	125	$^{\circ}\text{C}$	
$F_m$	Clamping force		20.0	25.0	kN	

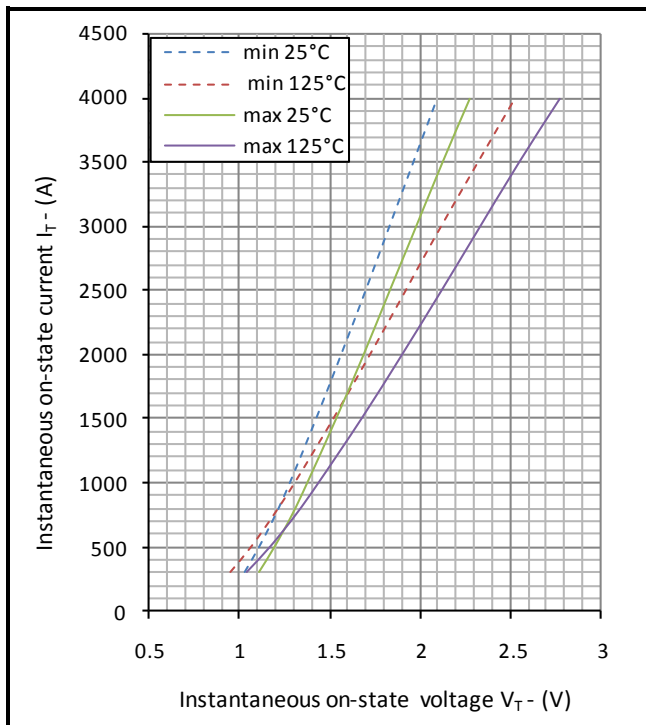
**DYNAMIC CHARACTERISTICS**

Symbol	Parameter	Test Conditions	Min.	Max.	Units	
$I_{RRM}/I_{DRM}$	Peak reverse and off-state current	At $V_{RRM}/V_{DRM}$ , $T_{case} = 125^{\circ}C$	-	100	mA	
$dV/dt$	Max. linear rate of rise of off-state voltage	To 67% $V_{DRM}$ , $T_j = 125^{\circ}C$ , gate open	-	1500	V/ $\mu$ s	
$dI/dt$	Rate of rise of on-state current	From 67% $V_{DRM}$ to $2x I_{T(AV)}$	Repetitive 50Hz	-	250	A/ $\mu$ s
		Gate source 30V, 10 $\Omega$ , $t_r < 0.5\mu$ s, $T_j = 125^{\circ}C$	Non-repetitive	-	1000	A/ $\mu$ s
$V_{T(TO)}$	Threshold voltage – Low level	300A to 850A at $T_{case} = 125^{\circ}C$	-	0.86	V	
	Threshold voltage – High level	850A to 4000A at $T_{case} = 125^{\circ}C$	-	1.0	V	
$r_T$	On-state slope resistance – Low level	300A to 850A at $T_{case} = 125^{\circ}C$	-	0.611	m $\Omega$	
	On-state slope resistance – High level	850A to 4000A at $T_{case} = 125^{\circ}C$	-	0.444	m $\Omega$	
$t_{gd}$	Delay time	$V_D = 67\% V_{DRM}$ , gate source 30V, 10 $\Omega$ $t_r = 0.5\mu$ s, $T_j = 25^{\circ}C$	-	3	$\mu$ s	
$t_q$	Turn-off time	$T_j = 125^{\circ}C$ , $V_R = 100V$ , $dI/dt = 5A/\mu$ s, $dV_{DR}/dt = 20V/\mu$ s linear to 2000V	-	800	$\mu$ s	
$Q_S$	Stored charge	$I_T = 1000A$ , $t_p = 1000\mu$ s, $T_j = 125^{\circ}C$ , $dI/dt = 5A/\mu$ s,	2000	3500	$\mu$ C	
$I_{RR}$	Reverse recovery current		81	121	A	
$I_L$	Latching current	$T_j = 25^{\circ}C$ , $V_D = 5V$	-	3	A	
$I_H$	Holding current	$T_j = 25^{\circ}C$ , $R_{G-K} = \infty$ , $I_{TM} = 500A$ , $I_T = 5A$	-	300	mA	

**GATE TRIGGER CHARACTERISTICS AND RATINGS**

Symbol	Parameter	Test Conditions	Max.	Units
V <sub>GT</sub>	Gate trigger voltage	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	1.5	V
V <sub>GD</sub>	Gate non-trigger voltage	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	0.4	V
I <sub>GT</sub>	Gate trigger current	V <sub>DRM</sub> = 5V, T <sub>case</sub> = 25°C	350	mA
I <sub>GD</sub>	Gate non-trigger current	At 50% V <sub>DRM</sub> , T <sub>case</sub> = 125°C	10	mA

**CURVES**



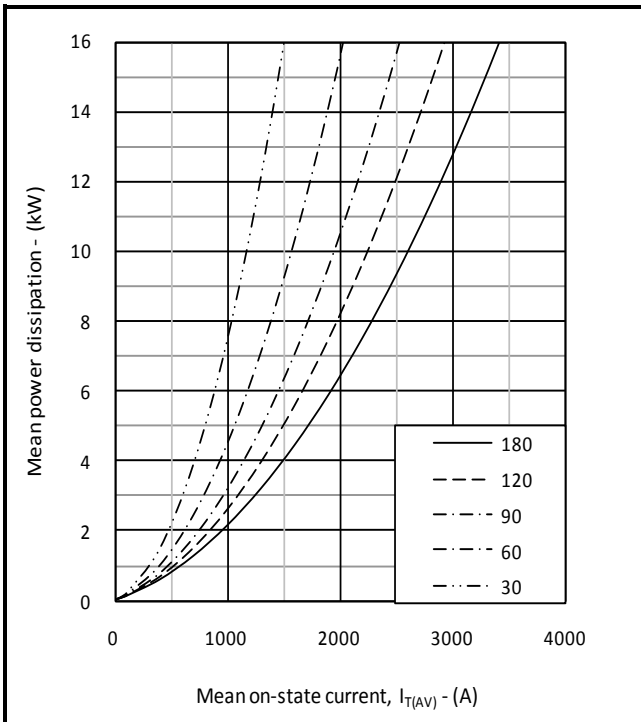
**Fig.2 Maximum & minimum on-state characteristics**

**V<sub>TM</sub> EQUATION**

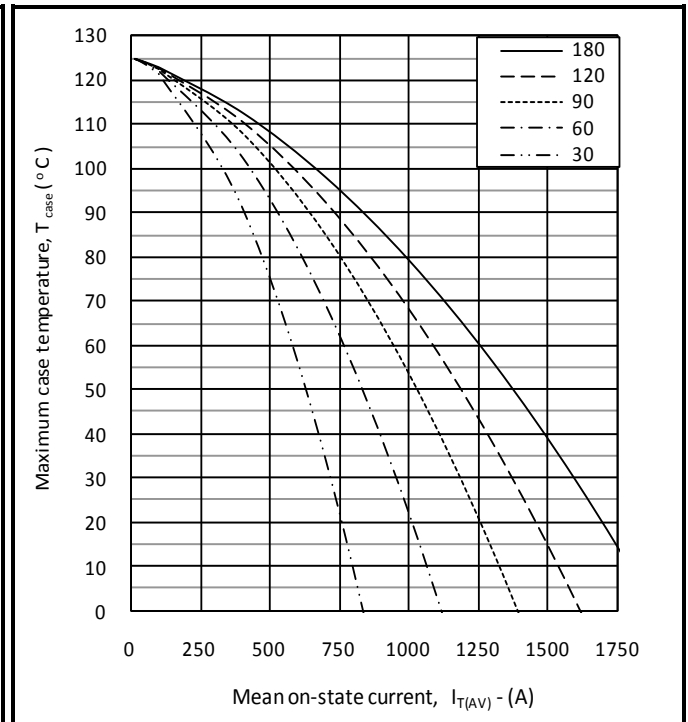
$$V_{TM} = A + B \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

Where A = 0.259886  
 B = 0.122742  
 C = 0.000418  
 D = -0.002452

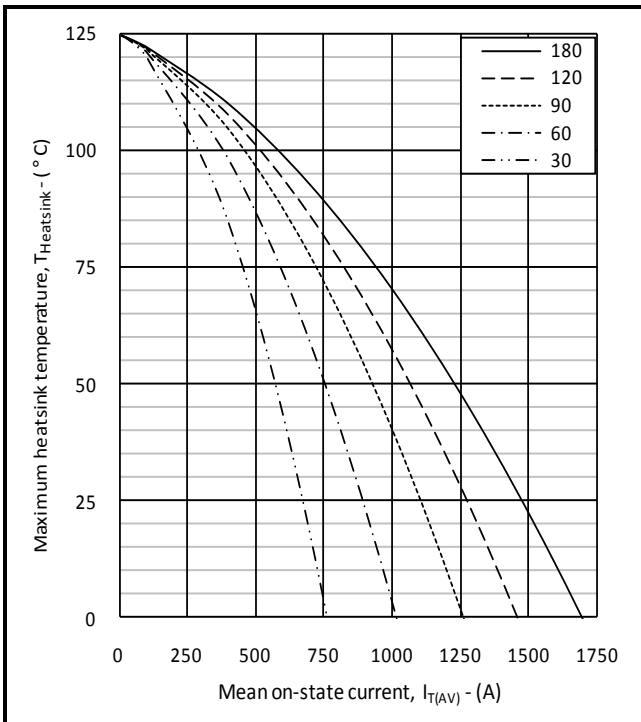
these values are valid for T<sub>j</sub> = 125°C for I<sub>T</sub> 300A to 4000A



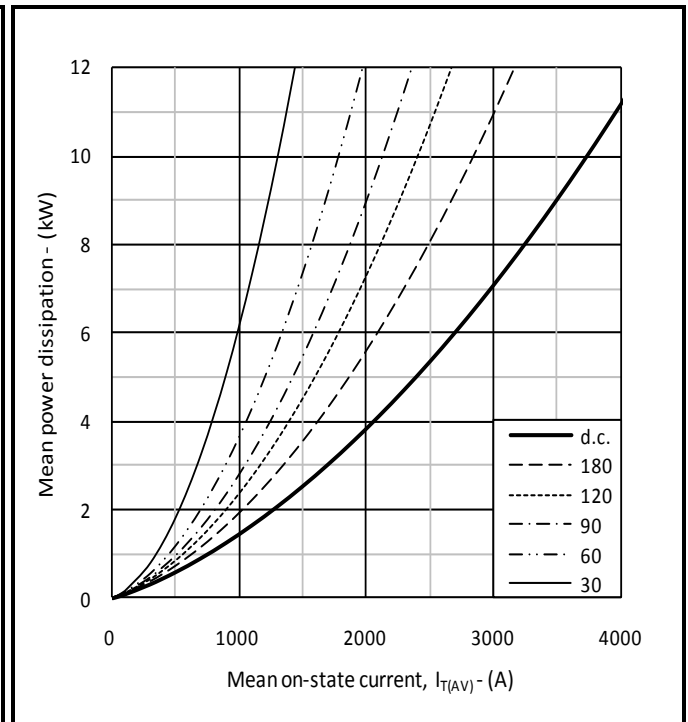
**Fig.3 On-state power dissipation – sine wave**



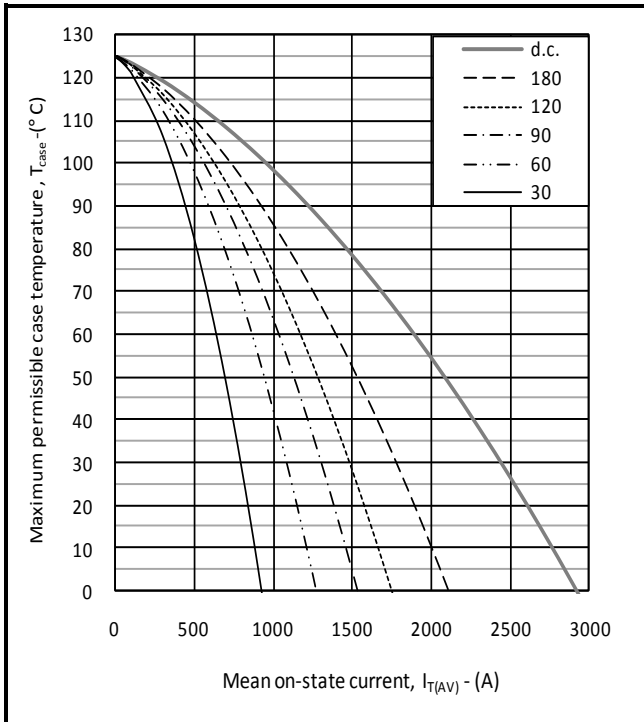
**Fig.4 Maximum permissible case temperature, double side cooled – sine wave**



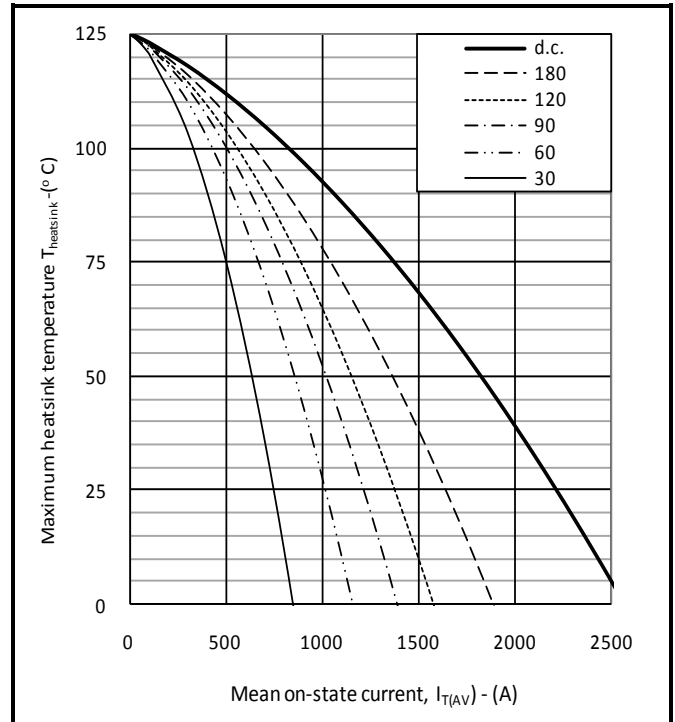
**Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave**



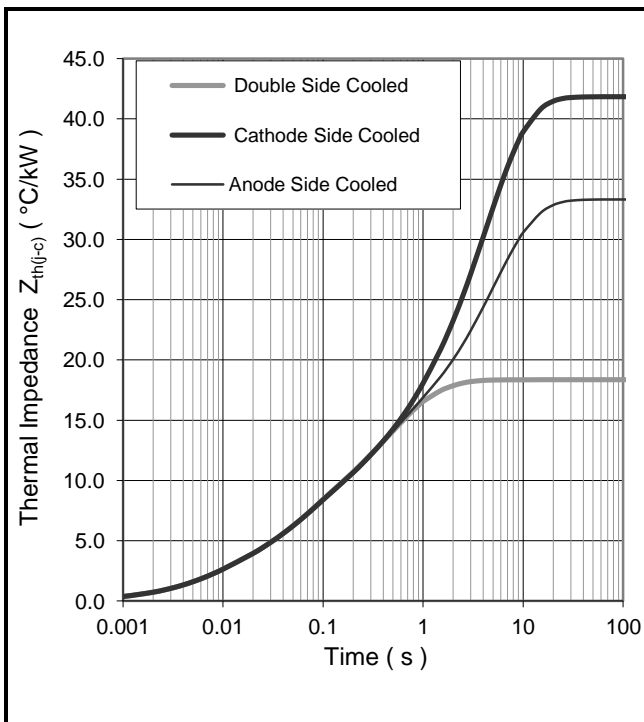
**Fig.6 On-state power dissipation – rectangular wave**



**Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave**



**Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave**



**Fig.9 Maximum (limit) transient thermal impedance – junction to case (°C/kW)**

		1	2	3	4
Double side cooled	R <sub>i</sub> (°C/kW)	7.5608	4.0772	3.8420	2.8671
	T <sub>i</sub> (s)	0.6877	0.2537	0.0614	0.0101
Anode side cooled	R <sub>i</sub> (°C/kW)	6.7211	4.6219	15.5387	14.8631
	T <sub>i</sub> (s)	0.1910	0.0158	5.0011	3.3169
Cathode side cooled	R <sub>i</sub> (°C/kW)	11.5564	8.5810	4.7942	8.3643
	T <sub>i</sub> (s)	4.2216	6.0269	0.0166	0.2255

$$Z_{th} = \sum_{i=1}^{i=4} [R_i \times (1 - \exp(-T / T_i))]$$

**ΔR<sub>th(j-c)</sub> Conduction**

Tables show the increments of thermal resistance R<sub>th(j-c)</sub> when the device operates at conduction angles other than d.c.

θ°	Double side cooling		Anode Side Cooling		Cathode Sided Cooling	
	sine.	rect.	sine.	rect.	sine.	rect.
180	3.19	2.14	2.97	2.03	2.95	2.02
120	3.72	3.10	3.43	2.89	3.40	2.87
90	4.29	3.64	3.92	3.36	3.88	3.34
60	4.81	4.23	4.36	3.87	4.31	3.84
30	5.22	4.88	4.69	4.41	4.64	4.37
15	5.40	5.22	4.84	4.70	4.79	4.65

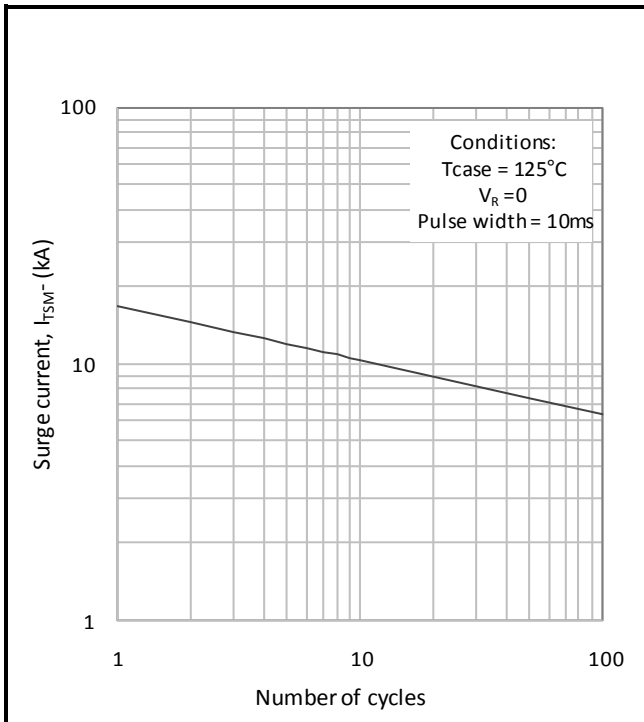


Fig.10 Multi-cycle surge current

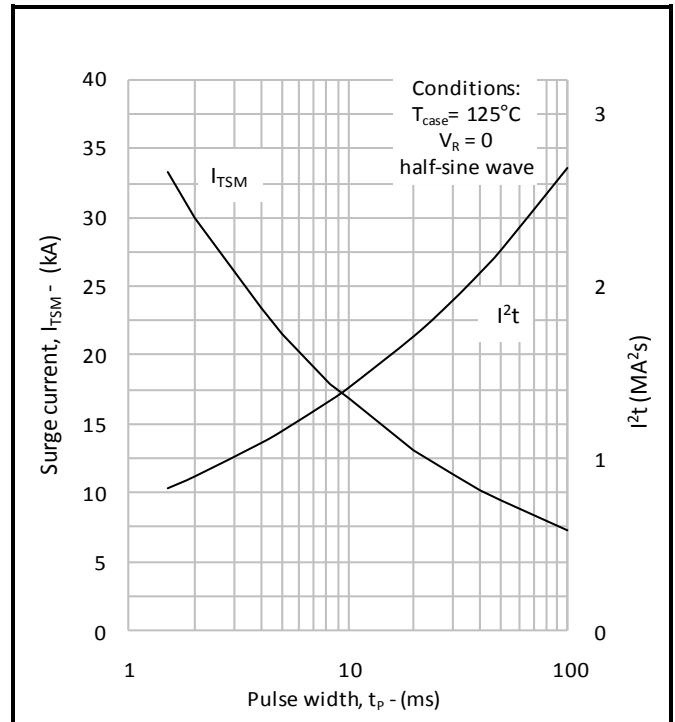


Fig.11 Single-cycle surge current

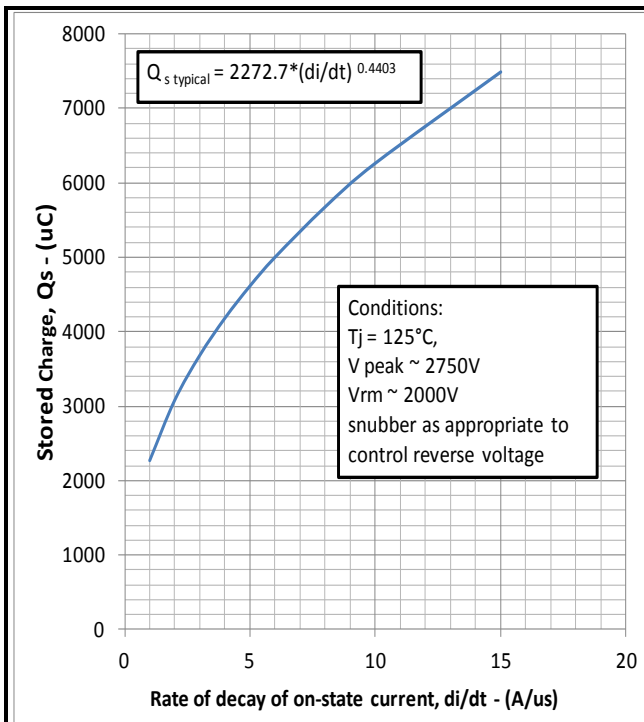


Fig.12 Stored charge vs di/dt

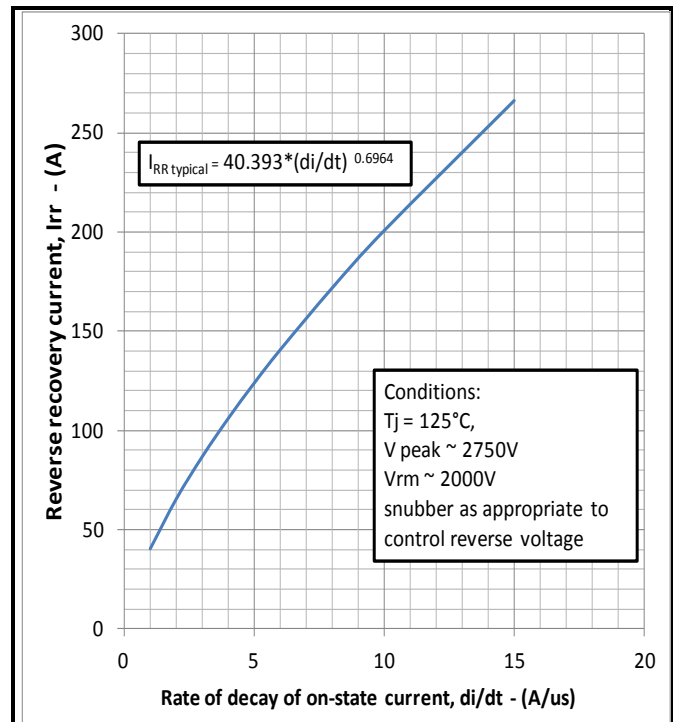


Fig.13 Reverse recovery current vs di/dt

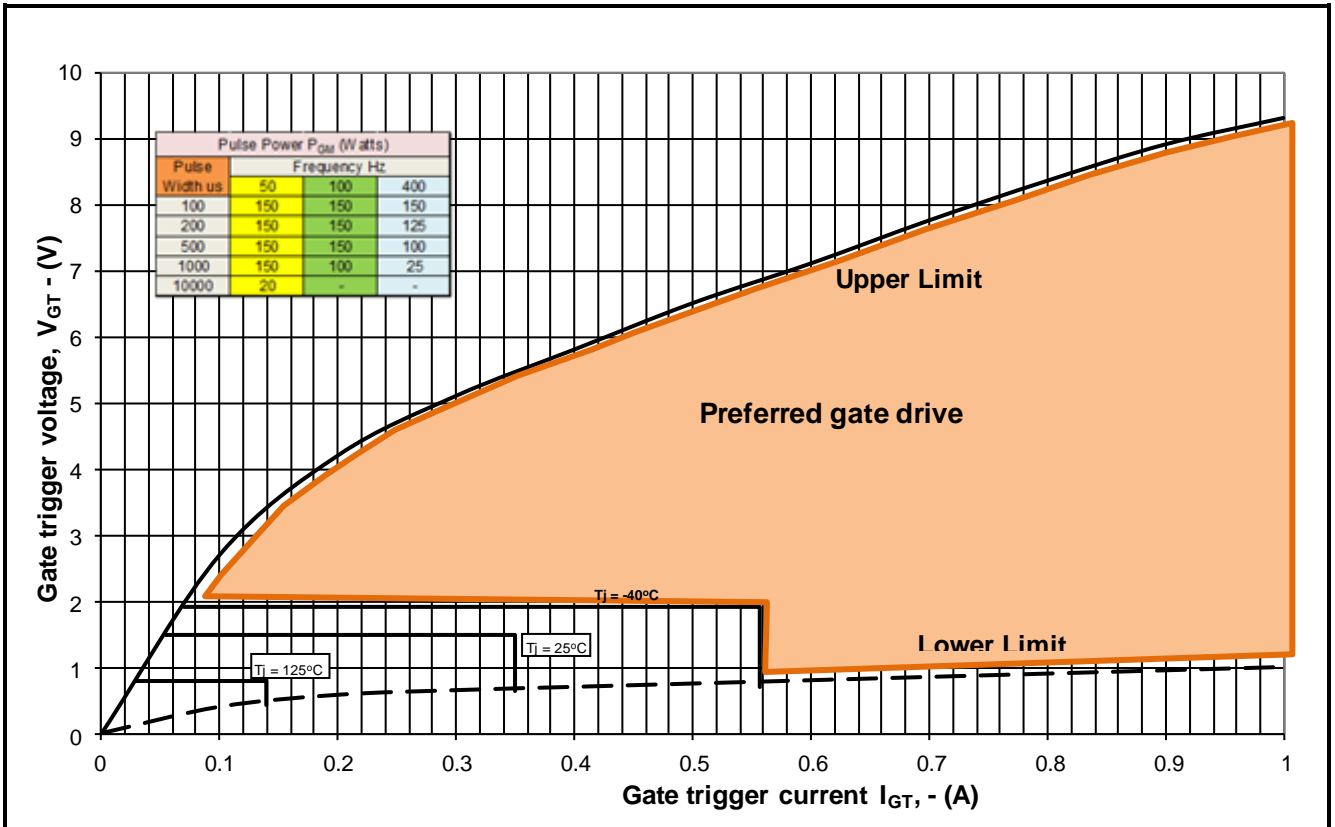


Fig14 Gate Characteristics

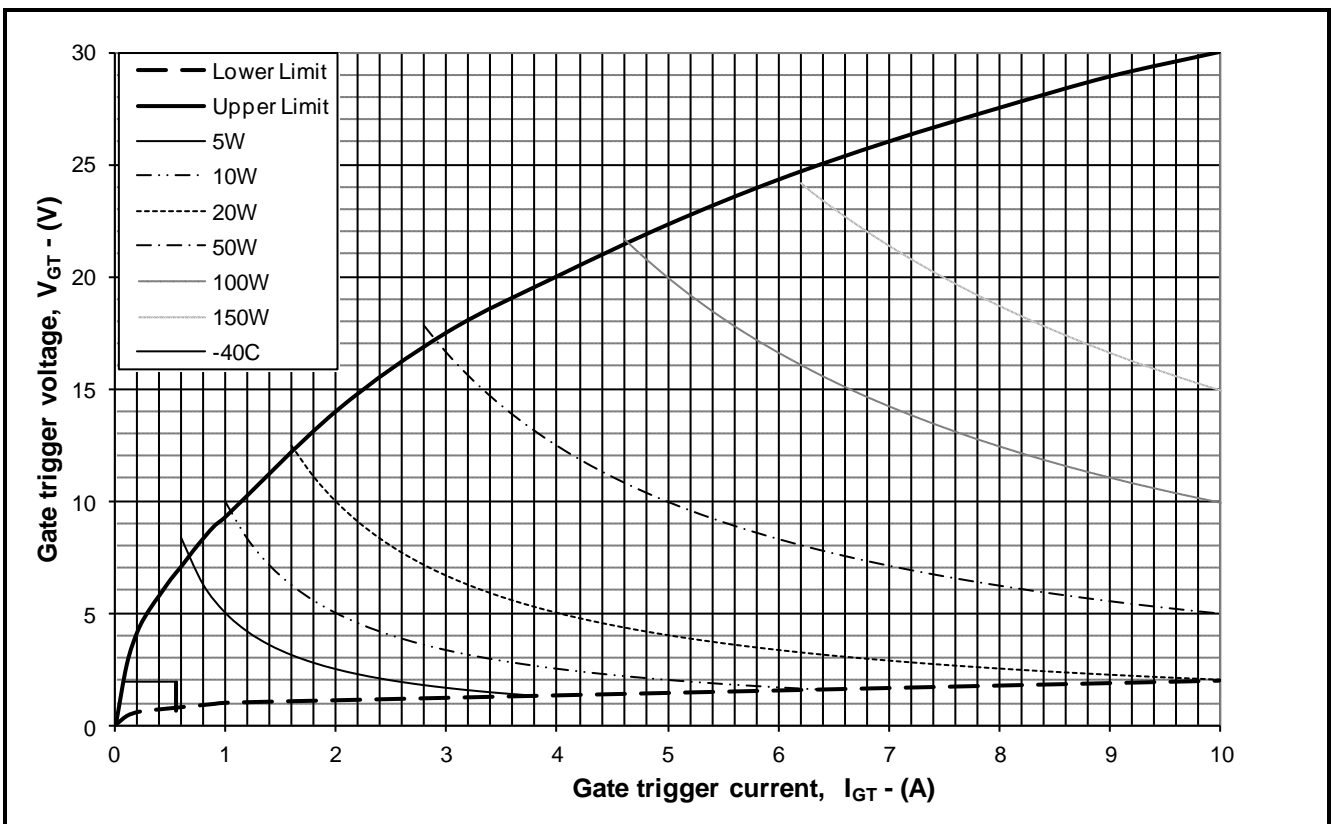
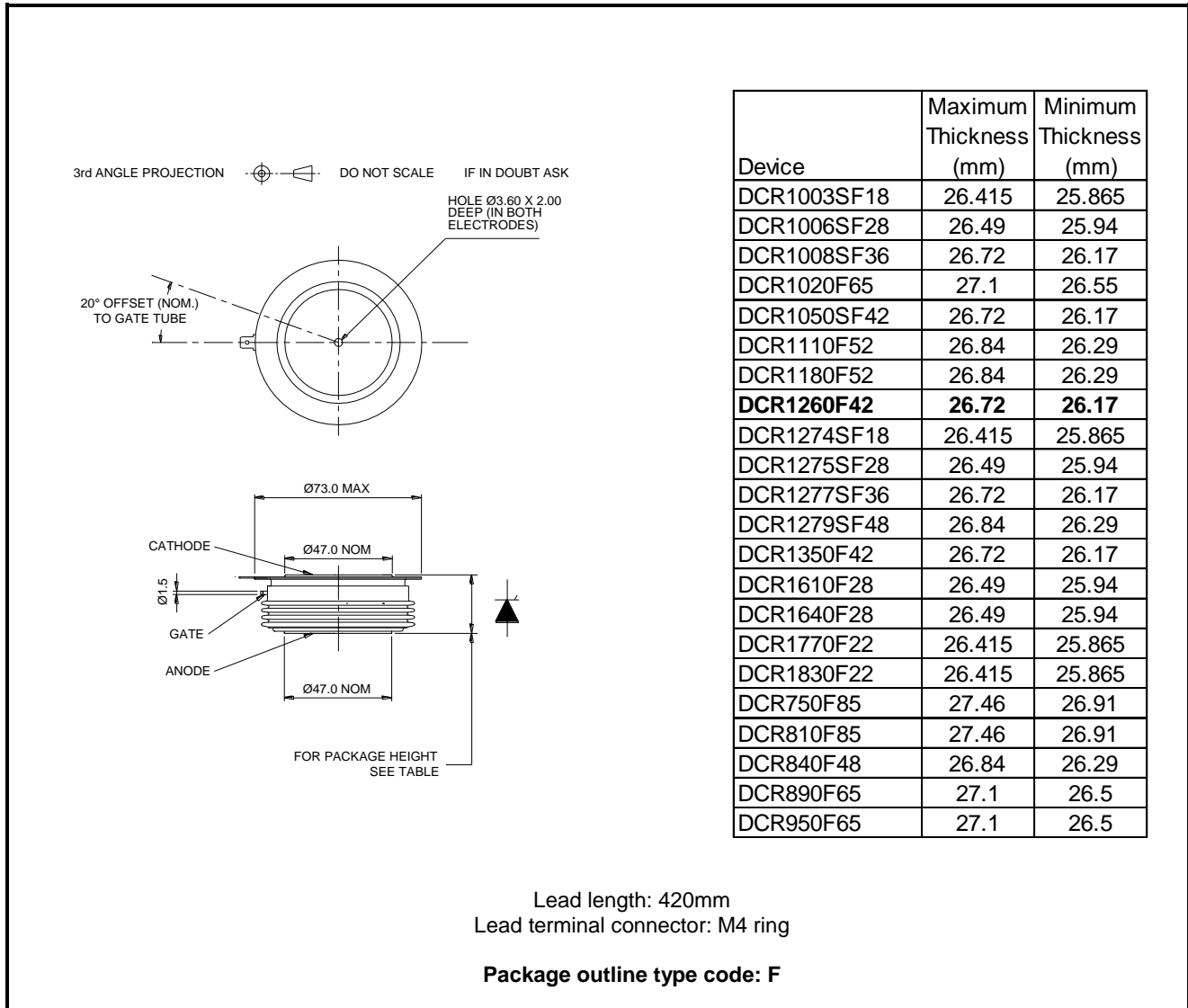


Fig. 15 Gate characteristics



**PACKAGE DETAILS**

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



**Fig.16 Package outline**

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**HEADQUARTERS OPERATIONS**

DYNEX SEMICONDUCTOR LIMITED  
Doddington Road, Lincoln, Lincolnshire, LN6 3LF  
United Kingdom.  
Phone: +44 (0) 1522 500500  
Fax: +44 (0) 1522 500550  
Web: <http://www.dynexsemi.com>

**CUSTOMER SERVICE**

Phone: +44 (0) 1522 502753 / 502901  
Fax: +44 (0) 1522 500020  
e-mail: [power\\_solutions@dynexsemi.com](mailto:power_solutions@dynexsemi.com)